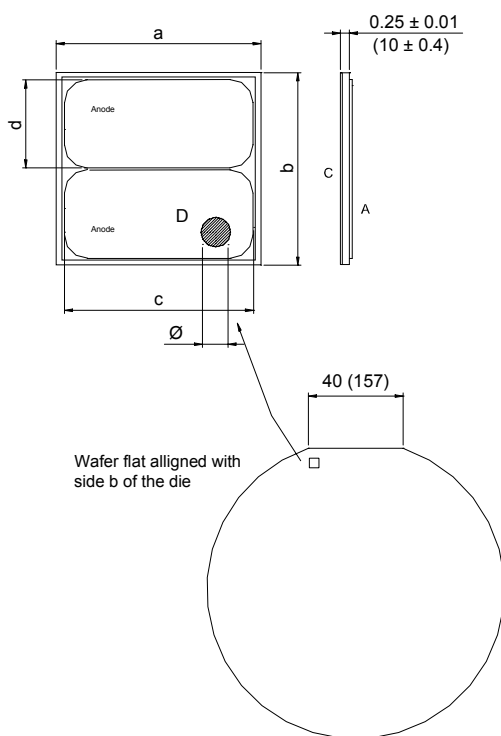


SCHOTTKY DIE 200 x 200 mils (Monolithic Dual)



NOTES:

1. ALL DIMENSIONS ARE SHOWN IN MILLIMETERS (MILS).
2. CONTROLLING DIMENSION: (MILS).
3. DIMENSIONS AND TOLERANCES:
  - $a = 5.08 + 0, - 0.01$   
(200 + 0, - 0.4)
  - $b = 5.08 + 0, - 0.01$   
(200 + 0, - 0.4)
  - $c = 4.92 + 0, - 0.01$   
(193 + 0, - 0.4)
  - $d = 2.43 + 0, - 0.01$   
(95 + 0, - 0.4)
  - $\varnothing = 1 \pm 0.15$   
(40  $\pm$  6)
4. LETTER DESIGNATION:
  - A = Anode (Top Metal)
  - C = Cathode (Back Metal)
  - D = Reject Ink Dot (only on non-conforming dies)
5. SAWING:
  - Recommended Blade
  - SEMITEC S1025 QS00 Blade
  - Sawing Street
  - $0.05 + 0, - 0.005$
  - (2 + 0, - 0.2)

NOT TO SCALE

## Electrical Characteristics

Device #	T <sub>J</sub> Max. (°C)	V <sub>R</sub> (V)	Max. I <sub>R</sub> @ 25°C (mA)	(*) Max. V <sub>F</sub> @ I <sub>F</sub> (V)
SC202 <b>S</b> 020A5	150	20	8	0.42 V @ 40A per die, T <sub>J</sub> = 25°C
SC202 <b>S</b> 030A5	150	30	2	0.46V @ 30A per die, T <sub>J</sub> = 25°C
SC202 <b>S</b> 045A5	150	45	2	0.51 V @ 20A per die, T <sub>J</sub> = 25°C
SC202 <b>S</b> 060A5	150	60	2	0.54V @ 15A per die, T <sub>J</sub> = 25°C
SC202 <b>H</b> 100A5	150	100	0.55	0.69 V @ 10A per die, T <sub>J</sub> = 25°C

(\*) For reference only, V<sub>F</sub> do not include voltage drop across wire bonding resistance

## Mechanical Data

Device #		Metal Thickness Front Metal			Metal Thickness Back Metal		
SC202..... <b>A</b> 5..	Bondable	–	Al/Si 30 kÅ	–	Ti 1 kÅ	Ni 4 kÅ	Ag 6 kÅ

Visual Inspection : see IR internal Spec. # 6373-2064

Recommended Storage Environment: Store in original container, in dessicated nitrogen, with no contamination.

Shelf life for parts stored in above condition is 2 years.

If the storage is done in normal atmosphere shelf life is reduced to six months.

## Packaging

Device #	Description	Minimum Order Quantity Wafer in Sale Package
SC202..... <b>5B</b> .	Inked Probed Unsawn Wafer (Wafer in Box)	48

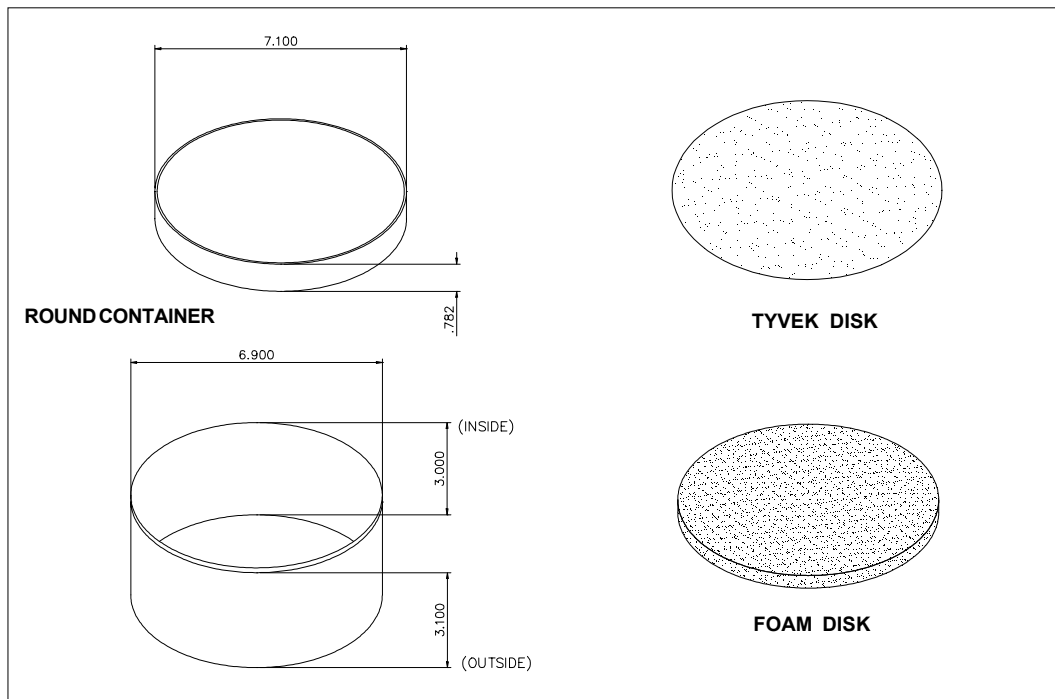
Ordering Information Table

Device Code						
<b>SC</b>	<b>202</b>	<b>S</b>	<b>060</b>	<b>A</b>	<b>5</b>	<b>B</b>
①	②	③	④	⑤	⑥	⑦

<ul style="list-style-type: none"> <li><b>1</b> - Schottky Die</li> <li><b>2</b> - Chip Dimension in Mils: 200 x 200 Dual Monolithic</li> <li><b>3</b> - Process (see Electrical Characteristics Table)</li> <li><b>4</b> - Voltage code: Code = <math>V_{RRM}</math></li> <li><b>5</b> - Chip surface metallization (Al)</li> <li><b>6</b> - Wafer Diameter in inches</li> <li><b>7</b> - Packaging: B = inked probed unsawn wafers (in box)</li> </ul>	<p>H = 830 Process  R = OR'ing Process  S = Standard Process</p>
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Wafer in Box



SC202.....5. Series

Preliminary Data Sheet I0508J rev. B 05/01

International  
**IOR** Rectifier

International  
**IOR** Rectifier

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Data and specifications subject to change without notice.